

L Number	Hits	Search Text	DB	Time stamp
1	5	"6368896"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 10:32
8	2	"6521041"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 12:26
15	7	"6328796"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 12:59
22	7	"6103597"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 14:16
29	143	(bond\$3 fus\$3) near12 (SiGe GeSi (Si?sub.\$3 near1 Ge?sub.\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 14:43
36	19	((bond\$3 fus\$3) near12 (SiGe GeSi (Si?sub.\$3 near1 Ge?sub.\$3))) and ((bond\$3 fus\$3 thermal thermally anneal\$3 heat\$3 bak\$3) near12 (nitrogen argon Ar "N.sub.2" air))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 17:47
43	313	(bond\$3 fus\$3) same (SiGe GeSi (Si?sub.\$3 near1 Ge?sub.\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 14:55
50	559145	((bond\$3 fus\$3 thermal thermally anneal\$3 heat\$3 bak\$3) near12 (nitrogen argon Ar "N.sub.2" air))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 14:47
57	662615	(bond\$3 fus\$3 thermal thermally anneal\$3 heat\$3 bak\$3) near12 (degree C)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 14:50
64	61503	((bond\$3 fus\$3 thermal thermally anneal\$3 heat\$3 bak\$3) near12 (nitrogen argon Ar "N.sub.2" air))) same ((bond\$3 fus\$3 thermal thermally anneal\$3 heat\$3 bak\$3) near12 (degree C))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 14:50
71	20	((bond\$3 fus\$3) same (SiGe GeSi (Si?sub.\$3 near1 Ge?sub.\$3))) and (((bond\$3 fus\$3 thermal thermally anneal\$3 heat\$3 bak\$3) near12 (nitrogen argon Ar "N.sub.2" air))) same ((bond\$3 fus\$3 thermal thermally anneal\$3 heat\$3 bak\$3) near12 (degree C)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 14:50
78	8	((bond\$3 fus\$3) same (SiGe GeSi (Si?sub.\$3 near1 Ge?sub.\$3))) and (((bond\$3 fus\$3 thermal thermally anneal\$3 heat\$3 bak\$3) near12 (nitrogen argon Ar "N.sub.2" air))) same ((bond\$3 fus\$3 thermal thermally anneal\$3 heat\$3 bak\$3) near12 (degree C)))) not (((bond\$3 fus\$3) near12 (SiGe GeSi (Si?sub.\$3 near1 Ge?sub.\$3))) and ((bond\$3 fus\$3 thermal thermally anneal\$3 heat\$3 bak\$3) near12 (nitrogen argon Ar "N.sub.2" air))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 14:50

85	62	((bond\$3 fus\$3) near12 (SiGe GeSi (Si?sub.\$3 near1 Ge?sub.\$3))) and ((bond\$3 fus\$3 thermal thermally anneal\$3 heat\$3 bak\$3) near12 (degree C))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 14:55
92	44	((bond\$3 fus\$3) near12 (SiGe GeSi (Si?sub.\$3 near1 Ge?sub.\$3))) and ((bond\$3 fus\$3 thermal thermally anneal\$3 heat\$3 bak\$3) near12 (degree C))) not (((bond\$3 fus\$3) near12 (SiGe GeSi (Si?sub.\$3 near1 Ge?sub.\$3))) and ((bond\$3 fus\$3 thermal thermally anneal\$3 heat\$3 bak\$3) near12 (nitrogen argon Ar "N.sub.2" air)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 17:10
99	86	"3332137" "3959045"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 15:32
106	4	"03037934" "02908787"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 17:00
114	3	"10237751"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 17:01
121	69	"5882987"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 17:01
128	2	5882987.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 17:01
135	21	"5906951"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 17:10
142	2	5906951.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 17:10
149	0	((bond\$3 fus\$3) near12 (SiGe GeSi (Si?sub.\$3 near1 Ge?sub.\$3))) and ((bond\$3 fus\$3 thermal thermally anneal\$3 heat\$3 bak\$3) near12 (nitrogen argon Ar "N.sub.2" air))) and (bonding near3 ambient)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 17:47

Set	Items	Description
	659	SIGE
	181	GESI
109329	SI	
55314	GE	
1515	SI(5N)GE	
46638	SILICON	
4459	GERMANIUM	
1655	SILICON(1N)GERMANIUM	
7159	RELAXED	
105295	BOND?	
6118	GRADED	
38866	GRADIENT	
10395	STEPPED	
S1	14	(SIGE OR GESI OR SI(5N)GE OR SILICON(1N)GERMANIUM) AND RELAXED AND BOND? AND (GRADED OR GRADIENT OR STEPPED)

?t s1/3/all

1/3/1

DIALOG(R)File 349:PCT FULLTEXT
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00865547 **Image available**

ETCH STOP LAYER SYSTEM

SYSTEME DE COUCHE D'ARRET DE GRAVURE *In French*

Patent Applicant/Assignee:

→ MASSACHUSETTS INSTITUTE OF TECHNOLOGY, 77 Massachusetts Avenue,
Cambridge, MA 02139, US, US (Residence), US (Nationality)

Inventor(s):

WU Kenneth C, 2695 California Street, #31, San Francisco, CA 94109, US,
FITZGERALD Eugene A, 7 Camelot Road, Windham, NH 03087, US,
BORENSTEIN Jeffrey T, 936 Highland Street, Holliston, MA 01746, US,
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Legal Representative:

CONNORS Matthew E (et al) (agent), Samuels, Gauthier & Stevens, LLP,
Suite 3300, 225 Franklin Street, Boston, MA 02110, US,

Patent and Priority Information (Country, Number, Date):

→ Patent: WO 200199169 A2 20011227 (WO 0199169)

→ Application: WO 2001US19613 20010620 (PCT/WO US0119613)

→ Priority Application: US 2000599260 20000622

Designated States: AL AM AT AU AZ BA BB BG BR BY CA CH CN CU CZ DE DK EE ES
FI GB GD GE GH GM HR HU ID IL IN IS JP KE KG KP KR KZ LC LK LR LS LT LU
LV MD MG MK MN MW MX NO NZ PL PT RO RU SD SE SG SI SK SL TJ TM TR TT UA
UG UZ VN YU ZW

(EP) AT BE CH CY DE DK ES FI FR GB GR IE IT LU MC NL PT SE TR

(OA) BF BJ CF CG CI CM GA GN GW ML MR NE SN TD TG

(AP) GH GM KE LS MW MZ SD SL SZ TZ UG ZW

(EA) AM AZ BY KG KZ MD RU TJ TM

Publication Language: English

Filing Language: English

Fulltext Word Count: 11193

1/3/2

DIALOG(R)File 349:PCT FULLTEXT
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00848083 **Image available**

COMPOSITIONS AND METHODS FOR THE THERAPY AND DIAGNOSIS OF ACNE VULGARIS
COMPOSITIONS ET PROCEDES POUR LA THERAPIE ET LE DIAGNOSTIC DE L'ACNE
VULGAIRE

Patent Applicant/Assignee:

CORIXA CORPORATION, 1124 Columbia Street, Suite 200, Seattle, WA 98104,

US, US (Residence) (Nationality), (For all designated states except: US)

Patent Applicant/Inventor:

SKEIKY Yasir A W, 15106 S.E. 47th Place, Bellevue, WA 98006, US, US
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(Residence), CN (Nationality), (Designated only for: US)
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(Residence), US (Nationality), (Designated only for: US)
CARTER Darrick, 321 Summit Avenue East, Seattle, WA 98102, US, US
(Residence), US (Nationality), (Designated only for: US)

Legal Representative:

POTTER Jane E R (et al) (agent), Seed Intellectual Property Law Group
PLLC, Suite 6300, 701 Fifth Avenue, Seattle, WA 98104-7092, US,

Patent and Priority Information (Country, Number, Date):

Patent: WO 200181581 A2 20011101 (WO 0181581)
Application: WO 2001US12865 20010420 (PCT/WO US0112865)
Priority Application: US 2000199047 20000421; US 2000208841 20000602; US
2000216747 20000707

Designated States: AE AG AL AM AT AU AZ BA BB BG BR BY BZ CA CH CN CO CR CU
CZ DE DK DM DZ EE ES FI GB GD GE GH GM HR HU ID IL IN IS JP KE KG KP KR
KZ LC LK LR LS LT LU LV MA MD MG MK MN MW MX MZ NO NZ PL PT RO RU SD SE
SG SI SK SL TJ TM TR TT TZ UA UG US UZ VN YU ZA ZW
(EP) AT BE CH CY DE DK ES FI FR GB GR IE IT LU MC NL PT SE TR
(OA) BF BJ CF CG CI CM GA GN GW ML MR NE SN TD TG
(AP) GH GM KE LS MW MZ SD SL SZ TZ UG ZW
(EA) AM AZ BY KG KZ MD RU TJ TM

Publication Language: English

Filing Language: English

Fulltext Word Count: 450843

1/3/3

DIALOG(R)File 349:PCT FULLTEXT

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00820626 **Image available**

**STRAINED-SILICON METAL OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTORS
TRANSISTORS A EFFET DE CHAMP, A SEMI-CONDUCTEUR METAL-OXYDE, ET A COUCHE DE
SILICIUM CONTRAINTE**

Legal Representative:

CONNORS Matthew E (et al) (agent), Samuels, Gauthier & Stevens, LLP,
Suite 3300, 225 Franklin Street, Boston, MA 02110, US,

Patent and Priority Information (Country, Number, Date):

Patent: WO 200154202 A1 20010726 (WO 0154202)
Application: WO 2001US1730 20010118 (PCT/WO US0101730)
Priority Application: US 2000177099 20000120

Designated States: CA JP

(EP) AT BE CH CY DE DK ES FI FR GB GR IE IT LU MC NL PT SE TR

Publication Language: English

Filing Language: English

Fulltext Word Count: 4362

1/3/4

DIALOG(R)File 349:PCT FULLTEXT

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00788952 **Image available**

METHOD OF PRODUCING RELAXED SILICON GERMANIUM LAYERS
PROCEDE DE PRODUCTION DE COUCHES DE SILICIUM-GERMANIUM DECONTRACTEES

Legal Representative:

CONNORS Matthew E (et al) (agent), Samuels, Gauthier & Stevens LLP, 225
Franklin Street, Suite 3300, Boston, MA 02110, US,

Patent and Priority Information (Country, Number, Date):

Patent: WO 200122482 A1 20010329 (WO 0122482)

Application: WO 2000US40938 20000919 (PCT/WO US0040938)

Priority Application: US 99154851 19990920 ,

Designated States: CA JP

(EP) AT BE CH CY DE DK ES FI FR GB GR IE IT LU MC NL PT SE

Publication Language: English

Filing Language: English

Fulltext Word Count: 1946

1/3/5

DIALOG(R) File 349:PCT FULLTEXT

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00740978 **Image available**

HIGH SPEED GE CHANNEL HETEROSTRUCTURES FOR FIELD EFFECT DEVICES
HETEROSTRUCTURES A CANAL GE GRANDE VITESSE POUR DISPOSITIFS A EFFET DE CHAMP

Patent Applicant/Assignee:

INTERNATIONAL BUSINESS MACHINES CORPORATION, New Orchard Road, Armonk, NY
10504, US, US (Residence), US (Nationality), (For all designated states
except: US)

Patent Applicant/Inventor:

CHU Jack O, 44 Shelbourne Lane, Manhasset Hills, NY 11040, US, US
(Residence), US (Nationality), (Designated only for: US)

Legal Representative:

TREPP Robert M, IBM Corporation, Intellectual Property Law Dept., P.O.
Box 218, Yorktown Heights, NY 10598, US

Patent and Priority Information (Country, Number, Date):

Patent: WO 200054338 A1 20000914 (WO 0054338)

Application: WO 2000US6258 20000311 (PCT/WO US0006258)

Priority Application: US 99124299 19990312

Designated States: CN JP KR SG US

(EP) AT BE CH CY DE DK ES FI FR GB GR IE IT LU MC NL PT SE

Publication Language: English

Filing Language: English

Fulltext Word Count: 20929

1/3/6

DIALOG(R) File 349:PCT FULLTEXT

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00737862 **Image available**

EVENT-RECORDING DEVICE HAVING AN IDENTIFICATION CODE
DISPOSITIF D'ENREGISTREMENT D'EVENEMENTS A CODES D'IDENTIFICATION

Patent Applicant/Assignee:

SRI INTERNATIONAL, 333 Ravenswood Avenue, Menlo Park, CA 94025, US, US
(Residence), US (Nationality)

Inventor(s):

WATTERS David G, 769 Prestwick Court, Sunnyvale, CA 94087, US

HUESTIS David L, 415 San Mateo Drive, Menlo Park, CA 94025, US

BAHR Alfred J, 2737 LaSalle Drive, Mountain View, CA 94040, US

Legal Representative:

WEAVER Jeffrey K, Beyer Weaver Thomas & Nguyen, LLP, P.O. Box 130,
Mountain View, CA 94042-0130, US

Patent and Priority Information (Country, Number, Date):

Patent: WO 200050849 A1 20000831 (WO 0050849)

Application: WO 2000US4998 20000225 (PCT/WO US0004998)

Priority Application: 99258073 19990226
Designated States: CA JP
(EP) AT BE CH CY DE DK ES FI FR GB GR IE IT LU MC NL PT SE
Publication Language: English
Filing Language: English
Fulltext Word Count: 21052

1/3/7

DIALOG(R)File 349:PCT FULLTEXT
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00735443

**HETEROEPITAXIAL GROWTH WITH THERMAL EXPANSION- AND LATTICE-MISMATCH
PROCEDE DE CONCEPTION DE STRUCTURES DE COUCHE EPITAXIALE ET DE SUBSTRAT
POUR UNE CROISSANCE EPITAXIALE DE HAUTE QUALITE SUR DES SUBSTRATS A
RESEAU DESADAPTE**

Patent Applicant/Assignee:

NOVA CRYSTALS INC, 30 Brown Road, Ithaca, NY 14850, US, US (Residence),
US (Nationality)

Inventor(s):

LO Yu-Hwa, 146 Lexington Drive, Ithaca, NY 14850, US
EJECKAM Felix E, 700 Warren Road, #17-1C, Ithaca, NY 14850, US
ZHU Zuhua, 134 Graham Road, Apt. 1B1, Ithaca, NY 14850, US

Legal Representative:

STUTIUS Wolfgang E, Foley, Hoag & Eliot LLP, One Post Office Square,
Boston, MA 02109, US

Patent and Priority Information (Country, Number, Date):

Patent: WO 200048239 A1 20000817 (WO 0048239)
Application: WO 2000US3023 20000204 (PCT/WO US0003023)
Priority Application: US 99247413 19990210

Designated States: JP

(EP) AT BE CH CY DE DK ES FI FR GB GR IE IT LU MC NL PT SE

Publication Language: English

Filing Language: English

Fulltext Word Count: 5751

1/3/8

DIALOG(R)File 349:PCT FULLTEXT
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00569981 **Image available**

**HIGH-EFFICIENCY HETEROSTRUCTURE THERMIONIC COOLERS
DISPOSITIFS DE REFROIDISSEMENT THERMOIONIQUES A HETEROSTRUCTURES**

Patent and Priority Information (Country, Number, Date):

Patent: WO 200033354 A2 20000608 (WO 0033354)
Application: WO 99US27284 19991117 (PCT/WO US9927284)
Priority Application: US 98109342 19981120

Designated States: JP AT BE CH CY DE DK ES FI FR GB GR IE IT LU MC NL PT SE

Publication Language: English

Fulltext Word Count: 8856

1/3/9

DIALOG(R)File 349:PCT FULLTEXT
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00549419

**COPOLYESTER BINDER FIBERS
FIBRES DE LIAISON DE CO-POLYESTER**

Patent Applicant/Assignee:

EASTMAN CHEMICAL COMPANY,

Inventor(s):

HAILE William Anston,
DEAN Leron Ronnie,
MCCONNELL Richard Leon,

Patent and Priority Information (Country, Number, Date):

Patent: WO 200012792 A1 20000309 (WO 0012792)

Application: WO 99US17830 19990806 (PCT/WO US9917830)

Priority Application: US 98143437 19980828; US 98187004 19981106

Designated States: BR CN JP MX AT BE CH CY DE DK ES FI FR GB GR IE IT LU MC
NL PT SE

Publication Language: English

Fulltext Word Count: 13926

1/3/10

DIALOG(R) File 349:PCT FULLTEXT

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00549418

POLYESTERS CONTAINING NEOPENTYL GLYCOL AND FIBERS FORMED THEREFROM

POLYESTERS CONTENANT DU NEOPENTYLGLYCOL ET FIBRES EN ETANT FAITES

Patent Applicant/Assignee:

EASTMAN CHEMICAL COMPANY,

Inventor(s):

HAILE William Anston,

DEAN Leron Ronnie,

MCCONNELL Richard Leon,

Patent and Priority Information (Country, Number, Date):

Patent: WO 200012791 A1 20000309 (WO 0012791)

Application: WO 99US17828 19990806 (PCT/WO US9917828)

Priority Application: US 98143437 19980828; US 98187004 19981106

Designated States: BR CN JP MX AT BE CH CY DE DK ES FI FR GB GR IE IT LU MC
NL PT SE

Publication Language: English

Fulltext Word Count: 11528

1/3/11

DIALOG(R) File 349:PCT FULLTEXT

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00522187

SILICON - GERMANIUM ETCH STOP LAYER SYSTEM

SYSTEME DE COUCHE D'ARRET D'ATTAQUE CHIMIQUE AU SILICIUM ET AU GERMANIUM

Patent Applicant/Assignee:

MASSACHUSETTS INSTITUTE OF TECHNOLOGY,

Inventor(s):

WU Kenneth C,

FITZGERALD Eugene A,

BORENSTEIN Jeffrey T,

Patent and Priority Information (Country, Number, Date):

Patent: WO 9953539 A1 19991021

Application: WO 99US7849 19990409 (PCT/WO US9907849)

Priority Application: US 9881301 19980410

Designated States: CA JP AT BE CH CY DE DK ES FI FR GB GR IE IT LU MC NL PT
SE

Publication Language: English

Fulltext Word Count: 7879

1/3/12

DIALOG(R) File 349:PCT FULLTEXT

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00378355

**NUCLEIC ACID AND AMINO ACID SEQUENCES RELATING TO HELICOBACTER PYLORI FOR
DIAGNOSTICS AND THERAPEUTICS**

**SEQUENCES D'ACIDES NUCLEIQUES ET D'ACIDES AMINES RELATIVES AU CODAGE DE
HELICOBACTER PYLORI A DES FINS DIAGNOSTIQUES ET THERAPEUTIQUES**

Patent Applicant/Assignee:

ASTRA AKTIEBOLAG,

SMITH Douglas H,
Inventor(s):
SMITH Douglas H,
Patent and Priority Information (Country, Number, Date):
Patent: WO 9719098 A1 19970529
Application: WO 96US18542 19961115 (PCT/WO US9618542)
Priority Application: US 95561469 19951117
Designated States: AL AM AT AU AZ BA BB BG BR BY CA CH CN CZ DE DK EE ES FI
GB GE HU IL IS JP KE KG KP KR KZ LC LK LR LS LT LU LV MD MG MK MN MW MX
NO NZ PL PT RO RU SD SE SG SI SK TJ TM TR TT UA UG US UZ VN KE LS MW SD
SZ UG AM AZ BY KG KZ MD RU TJ TM AT BE CH DE DK ES FI FR GB GR IE IT LU
MC NL PT SE BF BJ CF CG CI CM GA GN ML MR NE SN TD TG
Publication Language: English
Fulltext Word Count: 80181

1/3/13
DIALOG(R) File 349:PCT FULLTEXT
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00372505

~~METHOD AND APPARATUS FOR STORING AND RETRIEVING INFORMATION USING OPTICAL
DATA STORAGE MEDIA
PROCEDE PERMETTANT LA MEMORISATION ET LA RECUPERATION D'INFORMATIONS AU
MOYEN DE SUPPORTS OTIQUES DE STOCKAGE DE DONNEES ET APPAREIL
CORRESPONDANT~~

Patent Applicant/Assignee:

~~REVEO INC,
FAN Bunsen,
FARIS Sadeg M,~~

Inventor(s):

~~FAN Bunsen,
FARIS Sadeg M,~~

Patent and Priority Information (Country, Number, Date):

Patent: WO 9713247 A1 19970410
Application: WO 96US16604 19961004 (PCT/WO US9616604)
Priority Application: US 95539279 19951004

Designated States: AL AM AT AU AZ BB BG BR BY CA CH CN CZ DE DK EE ES FI GB
GE HU IL IS JP KE KG KP KR KZ LK LR LS LT LU LV MD MG MK MN MW MX NO NZ
PL PT RO RU SD SE SG SI SK TJ TM TR TT UA UG US UZ VN KE LS MW SD SZ UG
AM AZ BY KG KZ MD RU TJ TM AT BE CH DE DK ES FI FR GB GR IE IT LU MC NL
PT SE BF BJ CF CG CI CM GA GN ML MR NE SN TD TG

Publication Language: English

Fulltext Word Count: 45778

1/3/14
DIALOG(R) File 349:PCT FULLTEXT
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00348432 **Image available**

~~INTEGRATED HETEROSTRUCTURES OF GROUP III-V NITRIDE SEMICONDUCTOR MATERIALS
AND METHODS FOR FABRICATING THE SAME
HETEROSTRUCTURES INTEGRES A BASE DE SEMI-CONDUCTEURS DE NITRURES DU GROUPE
III-V ET LEUR PROCEDE DE FABRICATION~~

Patent Applicant/Assignee:

~~NORTH CAROLINA STATE UNIVERSITY,
SCHETZINA Jan Frederick,~~

Inventor(s):

~~SCHETZINA Jan Frederick,~~

Patent and Priority Information (Country, Number, Date):

Patent: WO 9630945 A2 19961003
Application: WO 96US4153 19960327 (PCT/WO US9604153)
Priority Application: US 95412971 19950329; US 95555604 19951109

Designated States: AL AM AT AT AU AZ BB BG BR BY CA CH CN CZ CZ DE DE DK DK
EE EE ES FI FI GB GE HU IS JP KE KG KP KR KZ LK LR LS LT LU LV MD MG MK
MN MW MX NO NZ PL PT RO RU SD SE SG SI SK SK TJ TM TR TT UA UG US UZ VN

✓ Your SELECT statement is
s (SiGe or GeSi or Si(5n)Ge or silicon(1n)germanium) and relaxed and
bond? and (graded or gradient or stepped)

useless →

Items	File
3	34: SciSearch(R) Cited Ref Sci_1990-2002/Jan W4
Examined 50 files	
1	340: CLAIMS(R)/US Patent 1950-02/JAN 29
18	348: EUROPEAN PATENTS 1978-2002/Jan W04
14	349: PCT FULLTEXT 1983-2002/UB=20020124,UT=20020117
2	370: Science 1996-1999/Jul W3
1	399: CA SEARCH(R) 1967-2002/UD=13605
1	652: US Patents Fulltext 1971-1979
6	653: US Patents Fulltext 1980-1989
63	654: US PAT.FULL. 1990-2002/JAN 29

*found PCT
of Wu, et al.
US PG Pub 2001/3269 A1

9 files have one or more items; file list includes 72 files.

?b 34;s (SiGe or GeSi or Si(5n)Ge or silicon(1n)germanium) and relaxed and bond? and (g
raded or gradient or stepped)

30jan02 11:44:04 User264704 Session D82.2

\$3.35 2.684 DialUnits File411

\$3.35 Estimated cost File411

\$0.30 TYMNET

\$3.65 Estimated cost this search

\$3.68 Estimated total session cost 2.886 DialUnits

File 34:SciSearch(R) Cited Ref Sci 1990-2002/Jan W4
(c) 2002 Inst for Sci Info

Set	Items	Description
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	4305	SIGE
--	------	------

	705	GESI
--	-----	------

	120437	SI
--	--------	----

	23136	GE
--	-------	----

	7139	SI(5N)GE
--	------	----------

	136505	SILICON
--	--------	---------

	11405	GERMANIUM
--	-------	-----------

	2965	SILICON(1N)GERMANIUM
--	------	----------------------

	11034	RELAXED
--	-------	---------

	236198	BOND?
--	--------	-------

	22514	GRADED
--	-------	--------

	100290	GRADIENT
--	--------	----------

	4682	STEPPED
--	------	---------

S1	3	(SIGE OR GESI OR SI(5N)GE OR SILICON(1N)GERMANIUM) AND RELAXED AND BOND? AND (GRADED OR GRADIENT OR STEPPED)
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?t s1/full/all

1/9/1

DIALOG(R)File 34:SciSearch(R) Cited Ref Sci

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06063142 Genuine Article#: XR964 Number of References: 16

Title: Group-IV semiconductor compounds

Author(s): Berding MA (REPRINT) ; Sher A; vanSchilfgaarde M

Corporate Source: SRI INT,333 RAVENSWOOD AVE/MENLO PK//CA/94025 (REPRINT)

Journal: PHYSICAL REVIEW B-CONDENSED MATTER, 1997, V56, N7 (AUG 15), P
3885-3891

ISSN: 0163-1829 Publication date: 19970815

Publisher: AMER INST PHYSICS, CIRCULATION FULFILLMENT DIV, 500 SUNNYSIDE
BLVD, WOODBURY, NY 11797-2999

Language: English Document Type: ARTICLE

Geographic Location: USA

Subfile: CC PHYS--Current Contents, Physical, Chemical & Earth Sciences

Journal Subject Category: PHYSICS, CONDENSED MATTER

Abstract: Properties of ordered group-IV compounds containing carbon, silicon, and germanium are calculated within the local density approximation. Twenty-seven fully relaxed compounds represented by seven-different compound structures are compared and, with the exception of SiC, all compounds are found to be metastable. Two trends emerge: carbon-germanium bonds are disfavored, and compounds that have carbon on a common sublattice are the least unbound because of their relatively low strain. When carbon shares a sublattice with silicon or germanium, the large strain results in a narrowing of the band gap, and in some cases the compound is metallic. The most promising structures with the lowest excess energy contain carbon on one sublattice and although they do not lattice match to silicon, they match rather well to silicon carbide.

Identifiers--KeyWord Plus(R): Si1-X-YGEXCY ALLOYS; GROWTH; STRAIN; SYSTEM

Research Fronts: 95-0888 002 (AB-INITIO PSEUDOPOTENTIAL CALCULATIONS; BAND-STRUCTURE IN ADAPTIVE CURVILINEAR COORDINATES; RANDOM METALLIC ALLOYS; GENERALIZED GRADIENT APPROXIMATION)

95-1042 002 (GRADIENT -CORRECTED DENSITY-FUNCTIONAL METHODS FOR TRANSITION-METAL COMPLEXES; VIBRATIONAL FREQUENCIES; PROTON-TRANSFER IN SMALL MODEL SYSTEMS)

95-5333 001 (EPITAXIAL Si1-X-YGEXCY ALLOYS; RAPID THERMAL CHEMICAL-VAPOR-DEPOSITION; SILICON MATRIX)

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VANSCHILFGAARDE M, UNPUB

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DIALOG(R) File 34:SciSearch(R) Cited Ref Sci
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05602595 Genuine Article#: WK088 Number of References: 36

Title: MeV ion implantation induced damage in relaxed Si1-xGex

Author(s): Larsen AN (REPRINT); ORaifeartaigh C; Barklie RC; Holm B;
Priolo F; Franzo G; Lulli G; Bianconi M; Nipoti R; Lindner JKN; Mesli A
; Grob JJ; Cristiano F; Hemment PLF

Corporate Source: AARHUS UNIV, INST PHYS & ASTRON/DK-8000 AARHUS C//DENMARK/
(REPRINT); UNIV DUBLIN TRINITY COLL, DEPT PHYS/DUBLIN 2//IRELAND//; UNIV
CATANIA, INFN/I-95129 CATANIA//ITALY//; UNIV CATANIA, DIPARTIMENTO
FIS/I-95129 CATANIA//ITALY//; CNR, IMETEM/I-95100 CATANIA//ITALY//;
LAMEL, CNR/I-40129 BOLOGNA//ITALY//; UNIV AUGSBURG, INST PHYS/D-86135
AUGSBURG//GERMANY//; CNRS, LAB PHASE, UPR 292/F-67037 STRASBOURG
2//FRANCE//; UNIV SURREY, DEPT ELECT & ELECT ENGN/GUILDFORD GU2
5XH/SURREY/ENGLAND/

Journal: JOURNAL OF APPLIED PHYSICS, 1997, V81, N5 (MAR 1), P2208-2218

ISSN: 0021-8979 Publication date: 19970301

Publisher: AMER INST PHYSICS, CIRCULATION FULFILLMENT DIV, 500 SUNNYSIDE
BLVD, WOODBURY, NY 11797-2999

Language: English Document Type: ARTICLE

Geographic Location: DENMARK; IRELAND; ITALY; GERMANY; FRANCE; ENGLAND

Subfile: CC PHYS--Current Contents, Physical, Chemical & Earth Sciences

Journal Subject Category: PHYSICS, APPLIED

1/9/3

DIALOG(R) File 34:SciSearch(R) Cited Ref Sci
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03206021 Genuine Article#: NM726 Number of References: 22

Title: ADSORPTION SITES OF GE ADATOMS ON STEPPED SI (110) SURFACE

Author(s): KATIRCIOGLU S; ERKOC S

Corporate Source: MIDDLE E TECH UNIV, DEPT PHYS/ANKARA 06531//TURKEY/;

MIDDLE E TECH UNIV, DEPT PHYS/ANKARA 06531//TURKEY/

Journal: SURFACE SCIENCE, 1994, V311, N3 (MAY 20), PL703-L706

ISSN: 0039-6028

Language: ENGLISH Document Type: LETTER

Geographic Location: TURKEY

Subfile: SciSearch; CC PHYS--Current Contents, Physical, Chemical & Earth
Sciences

Journal Subject Category: CHEMISTRY, PHYSICAL

Abstract: We have investigated the possible adsorption sites of Ge adatoms on stepped Si (110) surface by total electronic energy calculations using the empirical tight-binding method. It has been found that Ge adatoms prefer to bond to the Si atoms at or near the step. In the case of more than one adatom the minimum total electronic energy configuration corresponds to the maximum number of saturated Si atoms.

Identifiers--KeyWords Plus: 111 SURFACES; FILMS; SI; SI(001); GROWTH; LAYER

Research Fronts: 92-0137 001 (SIMGEN STRAINED LAYER SUPERLATTICES;
SEMICONDUCTOR QUANTUM HETEROSTRUCTURES; GAS SOURCE MOLECULAR-BEAM
EPITAXY; SURFACE STRUCTURAL-CHANGES)

92-0138 001 (GAS-SOURCE SI MOLECULAR-BEAM EPITAXY; STRAINED SILICON -
GERMANIUM ALLOY QUANTUM-WELLS; RELAXED GESI BUFFER LAYERS;
BAND-EDGE PHOTOLUMINESCENCE)

92-0551 001 (VICINAL SI(001) SURFACES; SI MBE GROWTH; SCANNING
TUNNELING MICROSCOPY; STEP STRUCTURE TRANSFORMATION)

92-1115 001 (QUANTUM WIRES; MOLECULAR-BEAM EPITAXY; NONPLANAR
SUBSTRATES; GROWTH OF GAAS; CARRIER CAPTURE; VICINAL GAAS(001)
SURFACES)

92-2101 001 (MISFIT DISLOCATIONS IN STRAINED LAYER EPITAXY; GROWTH
MODES; DELAYED RELAXATION)

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3	1449	1
4	1449	1

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